Michelle Y Simmons

List of Publications by Year
in descending order

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349 papers	11,423 citations	38742 50 h-index	39675 94 g-index
354 all docs	354 docs citations	354 times ranked	5938 citing authors

#	Article	IF	Citations
1	Silicon quantum electronics. Reviews of Modern Physics, 2013, 85, 961-1019.	45.6	892
2	A single-atom transistor. Nature Nanotechnology, 2012, 7, 242-246.	31.5	730
3	Possible Spin Polarization in a One-Dimensional Electron Gas. Physical Review Letters, 1996, 77, 135-138.	7.8	657
4	Atomically Precise Placement of Single Dopants in Si. Physical Review Letters, 2003, 91, 136104.	7.8	334
5	Ohmâ€™s Law Survives to the Atomic Scale. Science, 2012, 335, 64-67.	12.6	291
6	Metal-Insulator Transition atB=0in a Dilute Two Dimensional GaAs-AlGaAs Hole Gas. Physical Review Letters, 1998, 80, 1292-1295.	7.8	233
7	A two-qubit gate between phosphorus donor electrons in silicon. Nature, 2019, 571, 371-375.	27.8	222
8	Interaction effects in a one-dimensional constriction. Physical Review B, 1998, 58, 4846-4852.	3.2	221
9	A surface code quantum computer in silicon. Science Advances, 2015, 1, e1500707.	10.3	193
10	Spectroscopy of few-electron single-crystal silicon quantum dots. Nature Nanotechnology, 2010, 5, 502-505.	31.5	165
11	Spin-triplet negatively charged excitons in GaAs quantum wells. Physical Review B, 1995, 52, 7841-7844.	3.2	163
12	Toward Atomic-Scale Device Fabrication in Silicon Using Scanning Probe Microscopy. Nano Letters, 2004, 4, 1969-1973.	9.1	150
13	Spin blockade and exchange in Coulomb-confined silicon double quantum dots. Nature Nanotechnology, 2014, 9, 430-435.	31.5	117
14	Quenching of excitonic optical transitions by excess electrons in GaAs quantum wells. Physical Review B, 1995, 51, 18049-18052.	3.2	110
15	Precession and Motional Slowing of Spin Evolution in a High Mobility Two-Dimensional Electron Gas. Physical Review Letters, 2002, 89, 236601.	7.8	110
16	Realization of Atomically Controlled Dopant Devices in Silicon. Small, 2007, 3, 563-567.	10.0	108
17	Atomic-Scale, All Epitaxial In-Plane Gated Donor Quantum Dot in Silicon. Nano Letters, 2009, 9, 707-710.	9.1	104
18	Spin readout and addressability of phosphorus-donor clusters in silicon. Nature Communications, 2013, 4, 2017.	12.8	100

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19	Magnetization and Energy Gaps of a High-Mobility 2D Electron Gas in the Quantum Limit. Physical Review Letters, 1997, 79, 3238-3241.	7.8	96
20	Weak Localization, Hole-Hole Interactions, and the â€œMetalâ€•Insulator Transition in Two Dimensions. Physical Review Letters, 2000, 84, 2489-2492.	7.8	96
21	Encapsulation of phosphorus dopants in silicon for the fabrication of a quantum computer. Applied Physics Letters, 2002, 81, 3197-3199.	3.3	92
22	Spatially resolving valley quantum interference of a donor in silicon. Nature Materials, 2014, 13, 605-610.	27.5	90
23	Observation of Charge Transport by Negatively Charged Excitons. Science, 2001, 294, 837-839.	12.6	88
24	Hole-Hole Interaction Effect in the Conductance of the Two-Dimensional Hole Gas in the Ballistic Regime. Physical Review Letters, 2002, 89, 076406.	7.8	86
25	Zeeman Splitting in Ballistic Hole Quantum Wires. Physical Review Letters, 2006, 97, 026403.	7.8	85
26	Thermometer for the 2D Electron Gas using 1D Thermopower. Physical Review Letters, 1998, 81, 3491-3494.	7.8	81
27	Quantum simulation of the Hubbard model with dopant atoms in silicon. Nature Communications, 2016, 7, 11342.	12.8	81
28	Ballistic transport in oneâ€dimensional constrictions formed in deep twoâ€dimensional electron gases. Applied Physics Letters, 1995, 67, 109-111.	3.3	77
29	Fano Factor Reduction on the 0.7 Conductance Structure of a Ballistic One-Dimensional Wire. Physical Review Letters, 2004, 93, 116602.	7.8	75
30	Interaction Effects at Crossings of Spin-Polarized One-Dimensional Subbands. Physical Review Letters, 2003, 91, 136404.	7.8	73
31	Controlled wave-function mixing in strongly coupled one-dimensional wires. Physical Review B, 1999, 59, 12252-12255.	3.2	72
32	Detection of Coulomb Charging around an Antidot in the Quantum Hall Regime. Physical Review Letters, 1999, 83, 160-163.	7.8	67
33	Phosphine Dissociation on the Si(001) Surface. Physical Review Letters, 2004, 93, 226102.	7.8	65
34	On the acoustoelectric current in a one-dimensional channel. Journal of Physics Condensed Matter, 1996, 8, L337-L343.	1.8	63
35	Influence of doping density on electronic transport in degenerate Si:PÎ´-doped layers. Physical Review B, 2006, 73, .	3.2	62
36	Reentrant Insulator-Metal-Insulator Transition atB=0in a Two-Dimensional Hole Gas. Physical Review Letters, 1999, 82, 1542-1545.	7.8	60

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37	Progress in silicon-based quantum computing. Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences, 2003, 361, 1451-1471.	3.4	60
38	A Complete Fabrication Route for Atomic-Scale, Donor-Based Devices in Single-Crystal Germanium. Nano Letters, 2011, 11, 2272-2279.	9.1	60
39	Influence of excess electrons and magnetic fields on Mott-Wannier excitons in GaAs quantum wells. Advances in Physics, 1995, 44, 47-72.	14.4	59
40	Angle-resolved Raman spectroscopy of the collective modes in an electron bilayer. Physical Review B, 1999, 59, 2095-2101.	3.2	57
41	Thermal dissociation and desorption ofPH3on Si(001): A reinterpretation of spectroscopic data. Physical Review B, 2006, 74, .	3.2	57
42	Kondo Effect from a Tunable Bound State within a Quantum Wire. Physical Review Letters, 2008, 100, 026807.	7.8	57
43	Atomically engineered electron spin lifetimes of 30 s in silicon. Science Advances, 2017, 3, e1602811.	10.3	57
44	Two-electron spin correlations in precision placed donors in silicon. Nature Communications, 2018, 9, 980.	12.8	57
45	Fabrication of high-quality one- and two-dimensional electron gases in undoped GaAs/AlGaAs heterostructures. Applied Physics Letters, 1999, 74, 2328-2330.	3.3	54
46	Magnetization Instability in a Two-Dimensional System. Physical Review Letters, 1997, 79, 4449-4452.	7.8	51
47	Spin-dependent transport in a quasiballistic quantum wire. Physical Review B, 2000, 61, 9952-9955.	3.2	51
48	Experimental Evidence for Coulomb Charging Effects in an Open Quantum Dot at Zero Magnetic Field. Physical Review Letters, 1998, 81, 3507-3510.	7.8	50
49	Scanning probe microscopy for silicon device fabrication. Molecular Simulation, 2005, 31, 505-515.	2.0	50
50	Thermodynamic Density of States of Two-Dimensional GaAs Systems near the Apparent Metal-Insulator Transition. Physical Review Letters, 2006, 96, 216407.	7.8	50
51	Spin read-out in atomic qubits in an all-epitaxial three-dimensional transistor. Nature Nanotechnology, 2019, 14, 137-140.	31.5	50
52	Effect of spatial dispersion on acoustoelectric current in a high-mobility two-dimensional electron gas. Physical Review B, 1995, 51, 14770-14773.	3.2	49
53	Imaging cyclotron orbits and scattering sites in a high-mobility two-dimensional electron gas. Physical Review B, 2000, 62, 5174-5178.	3.2	49
54	Measurement of phosphorus segregation in silicon at the atomic scale using scanning tunneling microscopy. Applied Physics Letters, 2004, 85, 1359-1361.	3.3	49

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55	Weak localization in high-quality two-dimensional systems. Physical Review B, 2004, 70, .	3.2	49
56	Radio frequency measurements of tunnel couplings and singletâ€“triplet spin states in Si:P quantum dots. Nature Communications, 2015, 6, 8848.	12.8	49
57	High-Fidelity Rapid Initialization and Read-Out of an Electron Spin via the Single Donor<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msup><mml:mi>D</mml:mi><mml:mo>â^'</mml:mo></mml:msup></mml:math>Charge State. Physical Review Letters, 2015, 115, 166806.	7.8	48
58	Engineering topological states in atom-based semiconductor quantum dots. Nature, 2022, 606, 694-699.	27.8	48
59	Single-Shot Single-Gate rf Spin Readout in Silicon. Physical Review X, 2018, 8, .	8.9	47
60	Ultradense phosphorus in germanium delta-doped layers. Applied Physics Letters, 2009, 94, 162106.	3.3	45
61	Highly tunable exchange in donor qubits in silicon. Npj Quantum Information, 2016, 2, .	6.7	45
62	Spatial metrology of dopants in silicon with exact lattice site precision. Nature Nanotechnology, 2016, 11, 763-768.	31.5	45
63	Effect of encapsulation temperature on Si:P Î´-doped layers. Applied Physics Letters, 2004, 85, 4953-4955.	3.3	44
64	Phosphine adsorption and dissociation on the Si(001) surface: Anab initiosurvey of structures. Physical Review B, 2005, 72, .	3.2	44
65	Electronic structure of realistically extended atomistically resolved disordered Si:P<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>Î´</mml:mi></mml:math>-doped layers. Physical Review B, 2011, 84, .	3.2	44
66	Exploring the Limits of N-Type Ultra-Shallow Junction Formation. ACS Nano, 2013, 7, 5499-5505.	14.6	44
67	Magnetization measurements of high-mobility two-dimensional electron gases. Physical Review B, 2003, 67, .	3.2	43
68	Charge Sensing of Precisely Positioned P Donors in Si. Nano Letters, 2011, 11, 4376-4381.	9.1	43
69	New avenues to an old material: controlled nanoscale doping of germanium. Nanoscale, 2013, 5, 2600.	5.6	43
70	Conductance quantization and the 0.7Ã—2e2âˆ•h conductance anomaly in one-dimensional hole systems. Applied Physics Letters, 2006, 88, 012107.	3.3	42
71	Exploiting a Singleâ€Crystal Environment to Minimize the Charge Noise on Qubits in Silicon. Advanced Materials, 2020, 32, e2003361.	21.0	41
72	STM characterization of the Si-P heterodimer. Physical Review B, 2004, 69, .	3.2	40

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73	Electron-electron interactions in highly disordered two-dimensional systems. Physical Review B, 2008, 77, .	3.2	40
74	Engineering long spin coherence times of spinâ€“orbit qubits in silicon. Nature Materials, 2021, 20, 38-42.	27.5	40
75	Rapid radiative decay of charged excitons. Physical Review B, 2000, 62, R13294-R13297.	3.2	39
76	Impact of long- and short-range disorder on the metallic behaviour of two-dimensional systems. Nature Physics, 2008, 4, 55-59.	16.7	39
77	Investigating the regrowth surface of Si:P Î´-layers toward vertically stacked three dimensional devices. Applied Physics Letters, 2009, 95, .	3.3	39
78	Fabrication and transport properties of clean long one-dimensional quantum wires formed in modulation-doped GaAs/AlGaAs heterostructures. Applied Physics Letters, 1999, 75, 2975-2977.	3.3	37
79	Coulomb blockade of tunneling through compressible rings formed around an antidot: An explanation forh/2eAharonov-Bohm oscillations. Physical Review B, 2000, 62, R4817-R4820.	3.2	37
80	Kondo Effect in a Quantum Antidot. Physical Review Letters, 2002, 89, 226803.	7.8	37
81	Negatively charged excitons in coupled double quantum wells. Physical Review B, 1997, 55, 1318-1321.	3.2	36
82	Suppressing Segregation in Highly Phosphorus Doped Silicon Monolayers. ACS Nano, 2015, 9, 12537-12541.	14.6	36
83	Reaction paths of phosphine dissociation on silicon (001). Journal of Chemical Physics, 2016, 144, 014705.	3.0	36
84	Addressable electron spin resonance using donors and donor molecules in silicon. Science Advances, 2018, 4, eaaq1459.	10.3	36
85	Fermi-Liquid Behavior of the Low-Density 2D Hole Gas in aGaAs/AlGaAsHeterostructure at Large Values ofrs. Physical Review Letters, 2001, 86, 4895-4898.	7.8	35
86	Imaging charged defects on clean Si(100)-(2Ã—1) with scanning tunneling microscopy. Journal of Applied Physics, 2002, 92, 820-824.	2.5	35
87	Temperature-dependent Landau damping of the acoustic plasmon in a bilayer system. Physical Review B, 1998, 57, R2065-R2068.	3.2	34
88	High-Fidelity Single-Shot Singlet-Triplet Readout of Precision-Placed Donors in Silicon. Physical Review Letters, 2017, 119, 046802.	7.8	34
89	Temperature dependence of the breakdown of the quantum Hall effect studied by induced currents. Physical Review B, 2004, 70, .	3.2	33
90	One-dimensional conduction properties of highly phosphorus-doped planar nanowires patterned by scanning probe microscopy. Physical Review B, 2007, 76, .	3.2	33

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91	Energy-level pinning and the 0.7 spin state in one dimension: GaAs quantum wires studied using finite-bias spectroscopy. Physical Review B, 2007, 75, .	3.2	32
92	Microscopic four-point-probe resistivity measurements of shallow, high density doping layers in silicon. Applied Physics Letters, 2012, 101, .	3.3	32
93	Experimental study of the acoustoelectric effects in GaAs-AlGaAs heterostructures. Journal of Physics Condensed Matter, 1995, 7, 7675-7685.	1.8	31
94	Electronic properties of atomically abrupt tunnel junctions in silicon. Physical Review B, 2007, 75, .	3.2	31
95	Engineering Independent Electrostatic Control of Atomic-Scale (â^¼4 nm) Silicon Double Quantum Dots. Nano Letters, 2012, 12, 4001-4006.	9.1	31
96	The Aharonov-Bohm effect in the fractional quantum Hall regime. Surface Science, 1996, 361-362, 17-21.	1.9	30
97	Resonant Rayleigh scattering by excitonic states laterally confined in the interface roughnessof GaAs/AlxGa1â^'xAs single quantum wells. Physical Review B, 1997, 55, 13752-13760.	3.2	30
98	Metallic Behavior in Dilute Two-Dimensional Hole Systems. Physical Review Letters, 2001, 87, 126802.	7.8	30
99	Fabrication of induced two-dimensional hole systems on (311)A GaAs. Journal of Applied Physics, 2006, 99, 023707.	2.5	30
100	Direct Measurement of the Band Structure of a Buried Two-Dimensional Electron Gas. Physical Review Letters, 2013, 110, 136801.	7.8	30
101	High-Sensitivity Charge Detection with a Single-Lead Quantum Dot for Scalable Quantum Computation. Physical Review Applied, 2016, 6, .	3.8	30
102	Benchmarking high fidelity single-shot readout of semiconductor qubits. New Journal of Physics, 2019, 21, 063011.	2.9	29
103	Phosphine Dissociation and Diffusion on Si(001) Observed at the Atomic Scale. Journal of Physical Chemistry B, 2006, 110, 3173-3179.	2.6	28
104	Single hydrogen atoms on the Si(001) surface. Physical Review B, 2007, 76, .	3.2	28
105	Atomic-scale patterning of hydrogen terminated Ge(001) by scanning tunneling microscopy. Nanotechnology, 2009, 20, 495302.	2.6	28
106	Atomistic modeling of metallic nanowires in silicon. Nanoscale, 2013, 5, 8666.	5.6	28
107	Epitaxial top-gated atomic-scale silicon wire in a three-dimensional architecture. Nanotechnology, 2013, 24, 045303.	2.6	28
108	Fabrication of high mobilityin situback-gated (311)A hole gas heterojunctions. Applied Physics Letters, 1997, 70, 2750-2752.	3.3	27

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109	Excitonic recombination processes in spin-polarized two-dimensional electron gases. Physical Review B, 1998, 58, R4227-R4230.	3.2	27
110	One-dimensional probability density observed using scanned gate microscopy. Journal of Physics Condensed Matter, 2000, 12, L735-L740.	1.8	27
111	0.7 Structure and Zero Bias Anomaly in Ballistic Hole Quantum Wires. Physical Review Letters, 2008, 100, 016403.	7.8	27
112	Spin-Lattice Relaxation Times of Single Donors and Donor Clusters in Silicon. Physical Review Letters, 2014, 113, 246406.	7.8	27
113	Coherent control of a donor-molecule electron spin qubit in silicon. Nature Communications, 2021, 12, 3323.	12.8	27
114	The use of etched registration markers to make four-terminal electrical contacts to STM-patterned nanostructures. Nanotechnology, 2005, 16, 2446-2449.	2.6	26
115	Scanning tunneling microscope based fabrication of nano- and atomic scale dopant devices in silicon: The crucial step of hydrogen removal. Journal of Applied Physics, 2007, 101, 034305.	2.5	26
116	Phosphorus atomic layer doping of germanium by the stacking of multiple Î´ layers. Nanotechnology, 2011, 22, 375203.	2.6	26
117	Readout and control of the spin-orbit states of two coupled acceptor atoms in a silicon transistor. Science Advances, 2018, 4, eaat9199.	10.3	26
118	Phase coherence, interference, and conductance quantization in a confined two-dimensional hole gas. Physical Review B, 1994, 49, 5101-5104.	3.2	25
119	Imaging diffraction-limited electronic collimation from a non-equilibrium one-dimensional ballistic constriction. Journal of Physics Condensed Matter, 2000, 12, L167-L172.	1.8	25
120	Origin of the Oscillator Strength of the Triplet State of a Trion in a Magnetic Field. Physical Review Letters, 2002, 89, 246805.	7.8	25
121	Split-off dimer defects on theSi(001)2Ã—1surface. Physical Review B, 2004, 69, .	3.2	25
122	Low resistivity, super-saturation phosphorus-in-silicon monolayer doping. Applied Physics Letters, 2014, 104, .	3.3	25
123	Narrow, highly P-doped, planar wires in silicon created by scanning probe microscopy. Nanotechnology, 2007, 18, 044023.	2.6	24
124	Effective mass theory of monolayer<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>Î´</mml:mi></mml:math>doping in the high-density limit. Physical Review B, 2012, 85, .	3.2	24
125	Phosphorus Molecules on Ge(001): A Playground for Controlled n-Doping of Germanium at High Densities. ACS Nano, 2013, 7, 11310-11316.	14.6	24
126	Comparison of optical and transport measurements of electron densities in quantum wells. Semiconductor Science and Technology, 1996, 11, 890-896.	2.0	23

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127	Towards the atomic-scale fabrication of a silicon-based solid state quantum computer. Surface Science, 2003, 532-535, 1209-1218.	1.9	23
128	Influence of encapsulation temperature on Ge:PÎ´-doped layers. Physical Review B, 2009, 80, .	3.2	23
129	Limits to Metallic Conduction in Atomic-Scale Quasi-One-Dimensional Silicon Wires. Physical Review Letters, 2014, 113, 246802.	7.8	23
130	Transport in Asymmetrically Coupled Donor-Based Silicon Triple Quantum Dots. Nano Letters, 2014, 14, 1830-1835.	9.1	23
131	Radio frequency reflectometry and charge sensing of a precision placed donor in silicon. Applied Physics Letters, 2015, 107, .	3.3	22
132	Spin-dependent transport in a clean one-dimensional channel. Physical Review B, 1999, 60, 10687-10690.	3.2	21
133	Quantum-dot electron occupancy controlled by a charged scanning probe. Physical Review B, 2002, 66, .	3.2	21
134	Bottom-up assembly of metallic germanium. Scientific Reports, 2015, 5, 12948.	3.3	21
135	Compressibility studies of double electron and double hole gas systems. Applied Physics Letters, 1996, 68, 3323-3325.	3.3	20
136	Nonlinear transport in a single-mode one-dimensional electron gas. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1998, 77, 1213-1218.	0.6	20
137	Phosphorus and hydrogen atoms on the (001) surface of silicon: A comparative scanning tunnelling microscopy study of surface species with a single dangling bond. Surface Science, 2006, 600, 318-324.	1.9	20
138	Surface gate and contact alignment for buried, atomically precise scanning tunneling microscopyâ€“patterned devices. Journal of Vacuum Science & Technology B, 2007, 25, 2562.	1.3	20
139	Ultralow-Noise Atomic-Scale Structures for Quantum Circuitry in Silicon. Nano Letters, 2016, 16, 5779-5784.	9.1	20
140	Metalâ€“insulator transition at B=0 in an ultra-low density two-dimensional hole gas. Physica B: Condensed Matter, 1998, 249-251, 705-709.	2.7	19
141	STM imaging of buried P atoms in hydrogen-terminated Si for the fabrication of a Si:P quantum computer. Thin Solid Films, 2004, 464-465, 23-27.	1.8	19
142	The Impact of Dopant Segregation on the Maximum Carrier Density in Si:P Multilayers. ACS Nano, 2015, 9, 7080-7084.	14.6	19
143	Probing the Quantum States of a Single Atom Transistor at Microwave Frequencies. ACS Nano, 2017, 11, 2444-2451.	14.6	19
144	<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>n</mml:mi></mml:math>-Type Doping of Germanium from Phosphine: Early Stages Resolved at the Atomic Level. Physical Review Letters, 2012, 109, 076101.	7.8	18

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145	Interplay between quantum confinement and dielectric mismatch for ultrashallow dopants. Physical Review B, 2013, 87, .	3.2	18
146	Valley Splitting in a Silicon Quantum Device Platform. Nano Letters, 2014, 14, 1515-1519.	9.1	18
147	Two-electron states of a group-V donor in silicon from atomistic full configuration interactions. Physical Review B, 2018, 97, .	3.2	18
148	Experimental investigation of the damping of low-frequency edge magnetoplasmons in GaAs-AlxGa1â^'xAs heterostructures. Physical Review B, 1994, 50, 1582-1587.	3.2	17
149	Electrical Characterization of Ordered Si:P Dopant Arrays. IEEE Nanotechnology Magazine, 2007, 6, 213-217.	2.0	17
150	Stacking of 2D Electron Gases in Ge Probed at the Atomic Level and Its Correlation to Low-Temperature Magnetotransport. Nano Letters, 2012, 12, 4953-4959.	9.1	17
151	Transport through a single donor in p-type silicon. Applied Physics Letters, 2013, 103, 043106.	3.3	17
152	Spontaneous Breaking of Time-Reversal Symmetry in Strongly Interacting Two-Dimensional Electron Layers in Silicon and Germanium. Physical Review Letters, 2014, 112, 236602.	7.8	17
153	Strain and electric field control of hyperfine interactions for donor spin qubits in silicon. Physical Review B, 2015, 91, .	3.2	17
154	Characterizing Si:P quantum dot qubits with spin resonance techniques. Scientific Reports, 2016, 6, 31830.	3.3	17
155	Spinâ€“orbit coupling in silicon for electrons bound to donors. Npj Quantum Information, 2018, 4, .	6.7	17
156	Electron Density Dependence of the Excitonic Absorption Thresholds of GaAs Quantum Wells. Physica Status Solidi A, 2000, 178, 465-470.	1.7	16
157	Electron correlations in an electron bilayer at finite temperature: Landau damping of the acoustic plasmon. Journal of Physics Condensed Matter, 2000, 12, 439-466.	1.8	16
158	Coulomb charging effects in an open quantum dot device. Journal of Physics Condensed Matter, 2001, 13, 9515-9534.	1.8	16
159	STM investigation of epitaxial Si growth for the fabrication of a Si-based quantum computer. Applied Surface Science, 2003, 212-213, 319-324.	6.1	16
160	Suppression of low-frequency noise in two-dimensional electron gas at degenerately doped Si:P<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>Î´</mml:mi></mml:mrow></mml:math>layers. Physical Review B, 2011, 83, .	3.2	16
161	Atomic layer doping of strained Ge-on-insulator thin films with high electron densities. Applied Physics Letters, 2013, 102, 151103.	3.3	16
162	Single-charge detection by an atomic precision tunnel junction. Applied Physics Letters, 2014, 104, .	3.3	16

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163	Disentangling phonon and impurity interactions in Î´-doped Si(001). Applied Physics Letters, 2014, 104, 173108.	3.3	16
164	Tunneling Statistics for Analysis of Spin-Readout Fidelity. Physical Review Applied, 2017, 8, .	3.8	16
165	Evolution of the bilayerÎ½=1quantum Hall state under charge imbalance. Physical Review B, 2005, 71, .	3.2	15
166	Anomalous spin-dependent behavior of one-dimensional subbands. Physical Review B, 2005, 72, .	3.2	15
167	Investigating the surface quality and confinement of Si:P at different growth temperatures. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 1180-1183.	2.7	15
168	Interface-induced heavy-hole/light-hole splitting of acceptors in silicon. Applied Physics Letters, 2015, 106, .	3.3	15
169	Multilayered gated lateral quantum dot devices. Applied Physics Letters, 2000, 76, 1134-1136.	3.3	14
170	Scanning tunneling microscopy imaging of charged defects on clean Si(100)-(2Ã—1). Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2003, 21, 1506-1509.	2.1	14
171	Importance of charging in atomic resolution scanning tunneling microscopy: Study of a single phosphorus atom in aSi(001)surface. Physical Review B, 2006, 74, .	3.2	14
172	Effect of screening long-range Coulomb interactions on the metallic behavior in two-dimensional hole systems. Physical Review B, 2008, 77, .	3.2	14
173	Optimizing dopant activation in Si:P double <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si0014.gif" overflow="scroll"><mml:mi mathvariant="normal">Î´</mml:mi><mml:mtext>-layers</mml:mtext></mml:math>. Journal of Crystal Growth, 2010, 312, 3247-3250.	1.5	14
174	A Tight-Binding Study of Single-Atom Transistors. Small, 2015, 11, 374-381.	10.0	14
175	Manifestation of a non-Abelian Berry phase in a<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>p</mml:mi></mml:math>-type semiconductor system. Physical Review B, 2016, 93, .	3.2	14
176	Localisation and the metalâ€“insulator transition in two dimensions. Physica B: Condensed Matter, 2001, 296, 21-31.	2.7	13
177	Tuning the electron transport properties of a one-dimensional constriction using hydrostatic pressure. Physical Review B, 2002, 65, .	3.2	13
178	Optical imaging of trion diffusion and drift in GaAs quantum wells. Physical Review B, 2003, 68, .	3.2	13
179	Enhancing electron transport in Si:P delta-doped devices by rapid thermal anneal. Applied Physics Letters, 2008, 93, 142105.	3.3	13
180	First-principles modelling of scanning tunneling microscopy using non-equilibrium Greenâ€™s functions. Frontiers of Physics in China, 2010, 5, 369-379.	1.0	13

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181	Development of a tunable donor quantum dot in silicon. Applied Physics Letters, 2010, 96, 043116.	3.3	13
182	Valley Filtering in Spatial Maps of Coupling between Silicon Donors and Quantum Dots. Physical Review X, 2018, 8, .	8.9	13
183	Huge positive magnetoresistance of GaAsâˆ•AlGaAs high electron mobility transistor structures at high temperatures. Applied Physics Letters, 2007, 90, 252106.	3.3	12
184	Radio-frequency reflectometry on large gated two-dimensional systems. Review of Scientific Instruments, 2008, 79, 123901.	1.3	12
185	Ohmic conduction of sub-10nm P-doped silicon nanowires at cryogenic temperatures. Applied Physics Letters, 2008, 92, 052101.	3.3	12
186	Lithography and doping in strained Si towards atomically precise device fabrication. Nanotechnology, 2014, 25, 145302.	2.6	12
187	Effect of finite quantum-well width on the compressibility of a two-dimensional electron gas. Physical Review B, 1997, 55, 6715-6718.	3.2	11
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